



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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P-CHANNEL J-FET

Screening in reference to MIL-PRF-19500 available

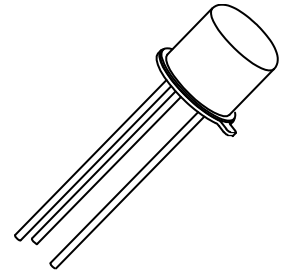
DESCRIPTION

This leaded device is available in high-reliability equivalents for high-reliability applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES


- Surface mount equivalent to JEDEC registered 2N5116.
- Screening in reference to MIL-PRF-19500 is available. (See [part nomenclature](#).)
- RoHS compliant versions available (commercial grade only).



TO-18 (TO-206AA) Package

Also available in:

UB package
(surface mount)

 [2N5114UB – 2N5116UB](#)

APPLICATIONS / BENEFITS

- Leaded TO-18 package.
- Lightweight.

MAXIMUM RATINGS @ $T_C = +25^\circ\text{C}$ unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-65 to +200	$^\circ\text{C}$
Gate-Source Voltage ⁽¹⁾	V_{GS}	30	V
Drain-Source Voltage	V_{DS}	30	V
Drain-Gate Voltage ⁽¹⁾	V_{DG}	30	V
Gate Current	I_G	50	mA
Steady-State Power Dissipation @ $T_A = +25^\circ\text{C}$ ⁽²⁾	P_D	0.500	W

- Notes:**
1. Symmetrical geometry allows operation of those units with source / drain leads interchanged.
 2. Derate linearly 3.0 mW/ $^\circ\text{C}$ for $T_A > +25^\circ\text{C}$.

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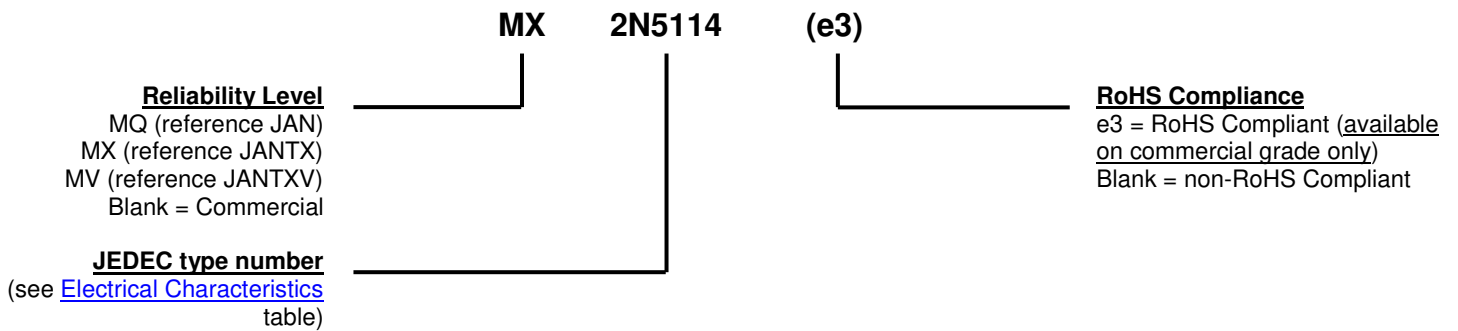
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MECHANICAL and PACKAGING

- CASE: Hermetically sealed, Nickel plated Kovar Base, Nickel Cap.
- TERMINALS: Gold plate over nickel, Kovar, Solder dipped. RoHS compliant Matte/Tin plating available on commercial grade only.
- MARKING: Part Number, Data Code, Manufacturer's ID.
- WEIGHT: Approximately 0.3 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE


ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ unless otherwise noted.

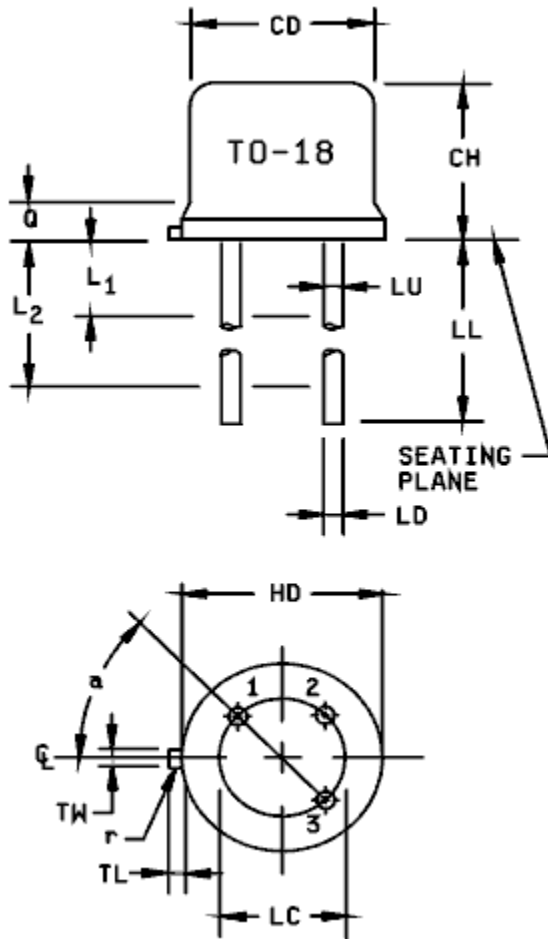
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate-Source Breakdown Voltage $V_{DS} = 0, I_G = 1.0 \mu\text{A}$	$V_{(BR)GSS}$	30		V
Drain-Source "On" State Voltage $V_{GS} = 0 \text{ V}, I_D = -15 \text{ mA}$ 2N5114 $V_{GS} = 0 \text{ V}, I_D = -7.0 \text{ mA}$ 2N5115 $V_{GS} = 0 \text{ V}, I_D = -3.0 \text{ mA}$ 2N5116	$V_{DS(on)}$		-1.3 -0.8 -0.6	V
Gate Reverse Current $V_{DS} = 0, V_{GS} = 20 \text{ V}$	I_{GSS}		500	pA
Drain Current Cutoff $V_{GS} = 12 \text{ V}, V_{DS} = -15 \text{ V}$ 2N5114 $V_{GS} = 7.0 \text{ V}, V_{DS} = -15 \text{ V}$ 2N5115 $V_{GS} = 5.0 \text{ V}, V_{DS} = -15 \text{ V}$ 2N5116	$I_{D(off)}$		-500 -500 -500	pA
Zero Gate Voltage Drain Current $V_{GS} = 0, V_{DS} = -18 \text{ V}$ 2N5114 $V_{GS} = 0, V_{DS} = -15 \text{ V}$ 2N5115 $V_{GS} = 0, V_{DS} = -15 \text{ V}$ 2N5116	I_{DSS}	-30 -15 -5.0	-90 -60 -25	mA
Gate-Source Cutoff $V_{DS} = -15, I_D = -1.0 \text{ nA}$ 2N5114 $V_{DS} = -15, I_D = -1.0 \text{ nA}$ 2N5115 $V_{DS} = -15, I_D = -1.0 \text{ nA}$ 2N5116	$V_{GS(off)}$	5.0 3.0 1.0	10 6.0 4.0	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Drain-Source "On" State Resistance $V_{GS} = 0, I_D = -1.0 \text{ mA}$ 2N5114 2N5115 2N5116	$r_{ds(on)1}$		75 100 175	Ω
Small-Signal Drain-Source "On" State Resistance $V_{GS} = 0, I_D = 0; f = 1 \text{ kHz}$ 2N5114 2N5115 2N5116	$r_{ds(on)2}$		75 100 175	Ω
Small-Signal, Common-Source Short-Circuit Reverse Transfer Capacitance $V_{GS} = 12 \text{ V dc}, V_{DS} = 0$ 2N5114 $V_{GS} = 7.0 \text{ V dc}, V_{DS} = 0$ 2N5115 $V_{GS} = 5.0 \text{ V dc}, V_{DS} = 0$ 2N5116	C_{rss}		7.0	pF
Small-Signal, Common-Source Short-Circuit Input Capacitance $V_{GS} = 0, V_{DS} = -15 \text{ V}, f = 1.0 \text{ MHz}$ 2N5114, 2N5115 2N5116	C_{iss}		25 27	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ unless otherwise noted. (continued)**SWITCHING CHARACTERISTICS**

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Turn-On Delay Time	2N5114	$T_{d(on)}$		6	ηs
	2N5115			10	
	2N5116			25	
Rise Time	2N5114	t_r		10	ηs
	2N5115			20	
	2N5116			35	
Turn-Off Delay Time	2N5114	$T_{d(off)}$		6	ηs
	2N5115			8	
	2N5116			20	

PACKAGE DIMENSIONS


Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.170	.210	4.32	5.33	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7,8
LL	.500	.750	12.70	19.05	7,8
LU	.016	.019	0.41	0.48	7,8
L ₁		.050		1.27	7,8
L ₂	.250		6.35		7,8
Q		.030		0.76	5
TL	.028	.048	0.71	1.22	3,4
TW	.036	.046	0.91	1.17	
r		.010		0.25	10
α	45° TP		45° TP		6
1, 2, 9, 11, 12					

NOTES:

1. Dimension are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TH shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by the gauge and gauging procedure shown in figure 2.
7. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
12. Lead 1 = source, lead 2 = gate, lead 3 = drain.